

## Features

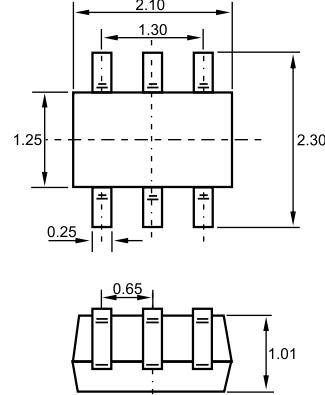
- ◊ Epitaxial Planar Die Construction
- ◊ Complementary NPN Type Available(MMDT 5551)
- ◊ Ideal for Medium Power Amplification and Switching

**MRKING:K4M**

### MAXIMUM RATINGS ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector- Base Voltage	-160	V
$V_{CEO}$	Collector-Emitter Voltage	-150	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_c$	Collector Current -Continuous	-0.2	A
$P_c$	Collector Power Dissipation	0.2	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55-150	$^\circ\text{C}$

### SOT-363



Dimensions in inches and (millimeters)

### ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}, I_E=0$	-160			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C= -1\text{mA}, I_B=0$	-150			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu\text{A}, I_C=0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-120 \text{ V}, I_E=0$			-0.05	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-3\text{V}, I_C=0$			-0.05	$\mu\text{A}$
DC current gain	$h_{FE(1)}$	$V_{CE}=-5 \text{ V}, I_C= -1\text{mA}$	50			
	$h_{FE(2)}$	$V_{CE}=-5 \text{ V}, I_C= -10\text{mA}$	60		240	
	$h_{FE(3)}$	$V_{CE}=-5 \text{ V}, I_C= -50\text{mA}$	50			
Collector-emitter saturation voltage	$V_{CE(sat)1}$	$I_C=-10 \text{ mA}, I_B=-1\text{mA}$			-0.2	V
	$V_{CE(sat)2}$	$I_C=-50 \text{ mA}, I_B=-5\text{mA}$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)1}$	$I_C= -10 \text{ mA}, I_B=-1\text{mA}$			-1	V
	$V_{BE(sat)2}$	$I_C= -50 \text{ mA}, I_B=-5\text{mA}$			-1	V
Transition frequency	$f_T$	$V_{CE}= -10\text{V}, I_C= -10\text{mA}, f = 100\text{MHz}$	100			MHz
Output Capacitance	$C_{ob}$	$V_{CB}=-10\text{V}, I_E= 0, f=1\text{MHz}$			6	pF
Noise Figure	NF	$V_{CE}= -5.0\text{V}, I_C= -200\mu\text{A}, R_S= 10\Omega, f = 1.0\text{kHz}$			8.0	dB

## Typical Characteristics

